HF150-50F

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF150-50S** is a 50 V epitaxial transistor designed for SSB communications. The device utilizes emitter ballastiong for ruggedness.

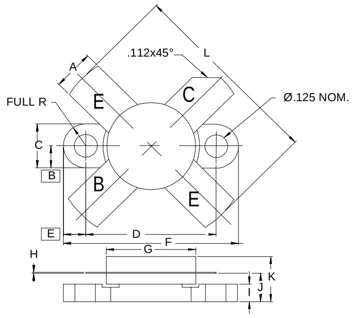
FEATURES:

- **P_G** = 14 dB min. at 150 W/30 MHz
- **IMD_3** = 100 dBc max. at 150 W(PEP)
- ***Omnigold***™ Metalization System
- Common Emitter configuration

MAXIMUM RATINGS

I_C	10 A
V_{CBO}	110 V
V_{CEO}	55 V
V_{EBO}	4.0 V
P_{DISS}	233 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.75 °C/W

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.7.30 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10612

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 100 mA	110			**V**
BV_{CES}	I_C = 100 mA	110			**V**
BV_{CEO}	I_C = 100 mA	55			**V**
BV_{EBO}	I_E = 10 mA	4.0			**V**
I_{CEO}	V_{CE} = 30 V			5	**mA**
I_{CES}	V_{CE} = 60 V			5	**mA**
h_{FE}	V_{CE} = 6 V I_C = 1.4 A	18		43.5	**---**
C_{ob}	V_{CB} = 50 V f = 1.0 MHz			220	**pF**
G_P	V_{CE} = 50 V I_{CQ} =100 mA P_{OUT} = 150 W(PEP) f_1 = 30.000 MHz f_2 = 30.001 MHz	14			**dB**
IMD_3				-30	**dBc**
η_C		37			**%**